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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Title: STRAINED SEMICONDUCTOR BY FULL WAFER BONDING

Docket No.: 1303.109US1
Filed: July 21, 2003
Examiner: Unknown

Serial No.: 10/623788
Due Date: N/A
Group Art Unit: 2811

Ms Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.
X A Communication Concerning Related Applications (2 pgs.).
X An Information Disclosure Statement (2 pgs.), Form 1449 (7 pgs.), and copies of 73 cited documents.

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: M L Bee
Atty: Marvin L. Beekman
Reg. No. 38,377

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JAMES KANYUSIK
Name

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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Serial No.:	10/623788	Group Art Unit: 2811
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COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
10/052952	January 17, 2002	1303.034US1	THREE-DIMENSIONAL PHOTONIC CRYSTAL WAVEGUIDE STRUCTURE AND METHOD
10/382246	March 5, 2003	1303.086US1	CELLULAR MATERIALS FORMED USING SURFACE TRANSFORMATION
10/379749	March 5, 2003	1303.089US1	MICRO-MECHANICALLY STRAINED SEMICONDUCTOR FILM
10/425797	April 29, 2003	1303.093US1	LOCALIZED STRAINED SEMICONDUCTOR ON INSULATOR
10/431134	May 7, 2003	1303.094US1	STRAINED Si/SiGe STRUCTURES BY ION IMPLANTATION
10/425484	April 29, 2003	1303.095US1	STRAINED SEMICONDUCTOR BY WAFER BONDING WITH MISORIENTATION
10/443340	May 21, 2003	1303.099US1	ULTRA-THIN SEMICONDUCTORS BONDED ON GLASS SUBSTRATES
10/431137	May 7, 2003	1303.100US1	MICROMECHANICAL STRAINED SEMICONDUCTOR BY WAFER BONDING
10/634174	August 5, 2003	1303.102US1	STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME

10/443337	May 21, 2003	1303.103US1	GETTERING OF SILICON ON INSULATOR USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS
10/443339	May 21, 2003	1303.104US1	WAFER GETTERING USING RELAXED SILICON GERMANIUM EPITAXIAL PROXIMITY LAYERS
10/623794	July 21, 2003	1303.108US1	GETTERING USING VOIDS FORMED BY SURFACE TRANSFORMATION
09/855532	May 16, 2001		METHOD OF FORMING MIRRORS BY SURFACE TRANSFORMATION OF EMPTY SPACES IN SOLID STATE MATERIALS
10/118350	April 14, 2004		METHOD OF FORMING SPATIAL REGIONS OF A SECOND MATERIAL IN A FIRST MATERIAL
10/093332	April 14, 2004		METHOD AND APPARATUS FOR PACKAGING SEMICONDUCTOR DEVICES

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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Date 5-10-04 By _____
Marvin L. Beekman
Reg. No. 38,377

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JAMES E. KAWYSIK
Name

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Serial No.:	10/623788	Group Art Unit:	2811
Filed:	July 21, 2003	Docket:	1303.109US1
Title:	STRAINED SEMICONDUCTOR BY FULL WAFER BONDING		

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

The present application is either a U.S. national patent application filed after June 30, 2003 or an international application that entered the national stage under 35 U.S.C. § 371 after June 30, 2003. Thus, Applicant believes that the U.S. Patent & Trademark Office has waived the requirement under 37 C.F.R. 1.98 (a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S. patent application publication. The waiver is provided in a pre-OG notice from the U.S. Patent & Trademark Office entitled "Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after

June 30, 2003" and dated July 11, 2003. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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Date 5-10-04 By Marvin L. Beekman
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JAMES E. KANYUSIK
Name

James E. Kanyusik
Signature

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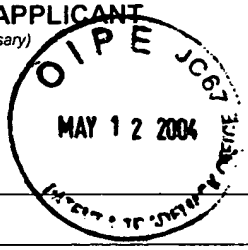

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Application Number	10/623788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

Sheet 1 of 7

Attorney Docket No: 1303.109US1

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Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** *(Use as many sheets as necessary)*	*Complete if Known*	
	Application Number	10/623788
	Filing Date	July 21, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2811
	Examiner Name	Unknown
Sheet 2 of 7	Attorney Docket No: 1303.109US1	

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Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Sheet 4 of 7

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Application Number	10/623788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

Sheet 6 of 7

Attorney Docket No: 1303.109US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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